

#### 20V PNP SILICON LOW SATURATION TRANSISTOR IN SOT23

#### Features

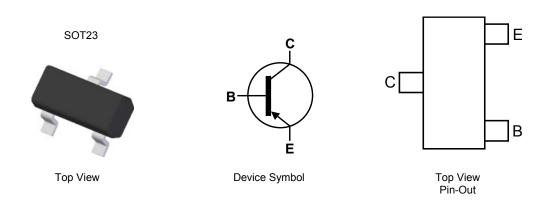
- BV<sub>CEO</sub> > -20V
- I<sub>C</sub> = -1.5A Continuous Collector Current
- I<sub>CM</sub> = -6A Peak Pulse Current
- Low Saturation Voltage V<sub>CE(sat)</sub> < -200mV @ -1A</li>
- $R_{CE(SAT)} = 97m\Omega$  for a low equivalent on-resistance
- 625mW power dissipation
- h<sub>FE</sub> characterized up to -6A for high current gain hold-up
- Complementary NPN Type: FMMT618Q
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen- and Antimony-Free. "Green" Device (Note 3)
- The FMMT718Q is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF16949 certified facilities. <u>https://www.diodes.com/quality/productdefinitions/</u>

### **Mechanical Data**

- Case: SOT23
- Case Material: Molded plastic, "Green" molding compound
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (2)
- Weight 0.008 grams (Approximate)

#### Applications

- Gate Driving MOSFETs and IGBTs
- DC-DC Converters
- Charging circuit
- Power switches



#### Ordering Information (Note 4)

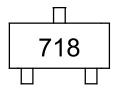
	Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
FN	1MT718QTA	Automotive	718	7	8	3,000
Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS). 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.						

No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.</p>

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

## **Marking Information**



718 = Product Type Marking Code



### Absolute Maximum Ratings (@ T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	-20	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-20	V
Emitter-Base Voltage	VEBO	-7	V
Continuous Collector Current	I <sub>C</sub>	-1.5	A
Peak Pulse Current	I <sub>CM</sub>	-6	A
Base Current	IB	-500	mA

## Thermal Characteristics (@ T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Power Dissipation (Note 5)	PD	625	mW	
Power Dissipation (Note 6)	PD	806	mW	
Thermal Resistance, Junction to Ambient (Note 5)	R <sub>0JA</sub>	200	°C/W	
Thermal Resistance, Junction to Ambient (Note 6)	R <sub>0JA</sub>	155	°C/W	
Thermal Resistance, Junction to Leads (Note 7)	R <sub>θJL</sub>	194	°C/W	
Operating and Storage Temperature Range	T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	٥°	

#### ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	≥ 400	V	С

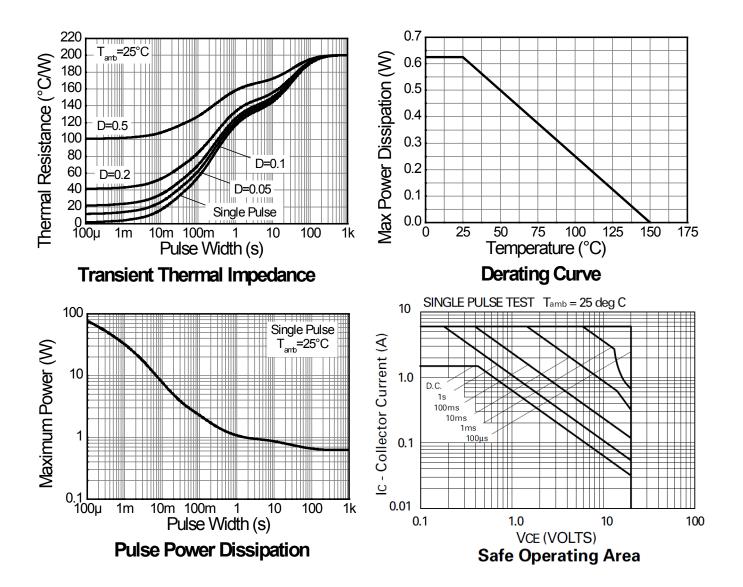
Notes: 5. For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1 oz copper, in still air conditions; the device is measured when operating in a steady-state condition.

6. Same as note 5, except the device is measured at t  $\leq$  5 sec.

Thermal resistance from junction to solder-point (at the end of the collector lead).
Refer to JEDEC specification JESD22-A114 and JESD22-A115.



## Thermal Characteristics and Derating information





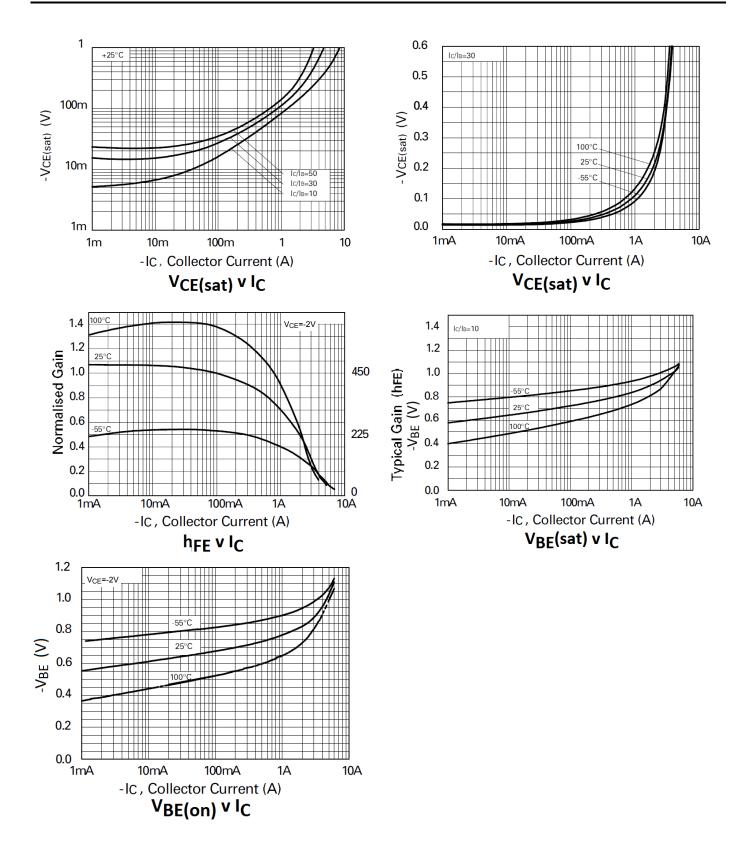
## Electrical Characteristics (@ T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	-20	-65	-	V	I <sub>C</sub> = -100μA
Collector-Emitter Breakdown Voltage (Note 9)	BV <sub>CEO</sub>	-20	-55	-	V	I <sub>C</sub> = -10mA
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	-7	-8.8	-	V	I <sub>E</sub> = -100μA
Collector Cutoff Current	Ісво	-	-	-100	nA	V <sub>CB</sub> = -15V
Emitter Cutoff Current	I <sub>EBO</sub>	-	-	-100	nA	V <sub>EB</sub> = -4V
Collector Emitter Cutoff Current	I <sub>CES</sub>	-	-	-100	nA	V <sub>CE</sub> = -15V
		300	475	-		I <sub>C</sub> = -10mA, V <sub>CE</sub> = -2V
		300	450	-		I <sub>C</sub> = -100mA, V <sub>CE</sub> = -2V
Static Forward Current Transfer Ratio (Note 9)	te 9) h <sub>FE</sub>	150	230	-	-	I <sub>C</sub> = -2A, V <sub>CE</sub> = -2V
		35	70	-		I <sub>C</sub> = -4A, V <sub>CE</sub> = -2V
		15	30	-		I <sub>C</sub> = -6A, V <sub>CE</sub> = -2V
		-	-16	-40	mV	I <sub>C</sub> =- 0.1A, I <sub>B</sub> = -10mA
Collector-Emitter Saturation Voltage (Note 9)	V <sub>CE(sat)</sub>	-	-130	-200	mV	I <sub>C</sub> = -1A, I <sub>B</sub> = -20mA
		-	-145	-220	mV	I <sub>C</sub> = -1.5A, I <sub>B</sub> = -50mA
Base-Emitter Turn-On Voltage(Note 9)	V <sub>BE(on)</sub>	-	-0.81	-1.0	V	I <sub>C</sub> = -2A, V <sub>CE</sub> = -2V
Base-Emitter Saturation Voltage(Note 9)	V <sub>BE(sat)</sub>	-	-0.87	-1.0	V	I <sub>C</sub> = -1.5A, I <sub>B</sub> = -50mA
Output Capacitance	Cobo	-	34	43	pF	V <sub>CB</sub> = -10V, f = 1MHz
Transition Frequency	f <sub>T</sub>	150	180	-	MHz	V <sub>CE</sub> = -10V, I <sub>C</sub> = -50mA, f = 100MHz
Turn-On Time	t <sub>on</sub>	-	68	-	ns	V <sub>CC</sub> = -10V, I <sub>C</sub> = -1A
Turn-Off Time	t <sub>off</sub>	-	270	-	ns	$I_{B1} = I_{B2} = -20 \text{mA}$

Notes: 9. Measured under pulsed conditions. Pulse width  $\leq$  300µs. Duty cycle  $\leq$  2%



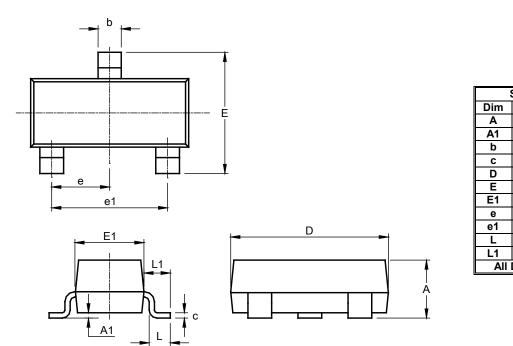
# Typical Electrical Characteristics (@ T<sub>A</sub> = +25°C, unless otherwise specified.)





## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.



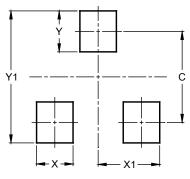
SOT23 (Type DN)

SOT23 Type DN						
Dim	Min	Max	Тур			
Α	0.89	1.12	1.00			
A1	0.01	0.10	0.05			
b	0.30 0.51 0.45					
С	0.08 0.20 0.10					
D	2.80	3.04	3.00			
E	2.10	2.64	2.42			
E1	1.20	1.40	1.37			
е	0.95 REF					
e1	1.90 REF					
L	0.25	0.60	0.30			
L1	0.45	0.62	0.54			
All Dimensions in mm						

## **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23 (Type DN)



Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Y	0.9
Y1	2.9



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